



WANSEMI
万芯半导体

WP8830

Enhancement Mode N-Channel Power MOSFET

TSSOP8/NMOS/20V/ ± 12 V/0.8V/10A/10m Ω

Rev1.0

20V, 10mΩ, 10A, N-Channel MOSFET

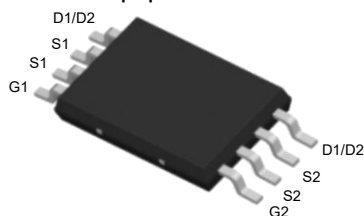
1.Features

- ◆ High Power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface Mount Package

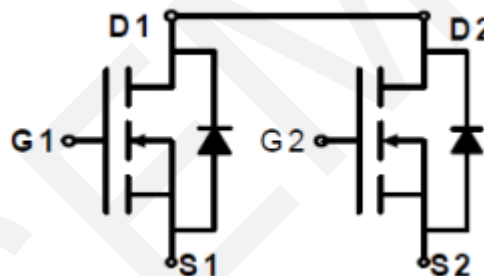
V _{DS} Typ.	R _{DS(on)} Typ.	I _D Max.
20V	10mΩ @ 4.5V	10A
	12.5mΩ @ 2.5V	

2.Applications

- ◆ Battery Protection
- ◆ Battery Powered Systems
- ◆ Power Management in Notebook Computer
- ◆ Portable Equipment



Pin Description
TSSOP8



Schematic Diagram

3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WP8830	8830	TSSOP8	5,000	80,000

4.Absolute Max Ratings at Ta=25°C (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V _{DSS}	20	V
Gate to Source Voltage	V _{GSS}	±12	V
Drain Current-Continuous	I _D	10	A
Drain Current (Pulse)	I _{DM}	40	A
Maximum Power Dissipation	P _D	1.5	W
Operating Junction and Storage Temperature Range	T _j , T _{stg}	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5. Thermal Resistance Ratings (Note 2)

Parameter	Symbol	Value	Unit
Maximum Junction-to-Ambien	$R_{\theta JA}$	64	$^{\circ}\text{C/W}$

Note 2: When mounted on 1 inch square copper board $t \leq 10\text{sec}$ The value in any given application depends on the user's specific board design.

6. Electrical Characteristics at $T_a=25^{\circ}\text{C}$ (Note 3)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	20	23	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 10\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{DS}=250\mu\text{A}$	0.5	0.8	1.2	V
Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = 6\text{A}$, $V_{GS} = 4.5\text{V}$	-	10	13	$\text{m}\Omega$
		$I_D = 5\text{A}$, $V_{GS} = 2.5\text{V}$	-	12.5	18	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$, $V_{DS}=10\text{V}$, Frequency=1.0MHz	-	290	-	pF
Output Capacitance	C_{oss}		-	120	-	pF
Reverse Transfer Capacitance	C_{rss}		-	40	-	pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{DS} = 10\text{V}$, $V_{GS} = 5\text{V}$, $R_{GEN} = 3\Omega$, $R_L = 1.7\Omega$	-	280	-	ns
Turn-ON Rise Time	t_r		-	972	-	ns
Turn-OFF Delay Time	$t_{d(off)}$		-	2.4	-	ns
Turn-ON Fall Time	t_f		-	2.2	-	ns
Total Gate Charge	Q_g	$V_{DS} = 10\text{V}$, $V_{GS} = 4.5\text{V}$, $I_D = 6\text{A}$	-	5.2	-	nC
Gate-Source Charge	Q_{gs}		-	2	-	nC
Gate-Drain Charge	Q_{gd}		-	1.9	-	nC
Diode Forward Voltage	V_{SD}	$I_S = 6\text{A}$, $V_{GS} = 0\text{V}$	-	0.75	1.2	V

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

7. Typical electrical and thermal characteristics

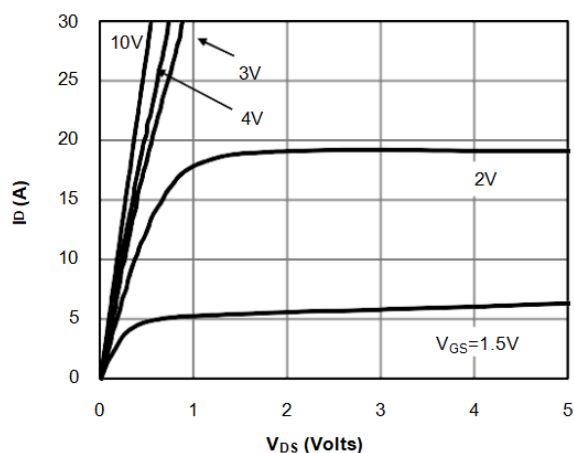


Figure 1 On-Region Characteristics

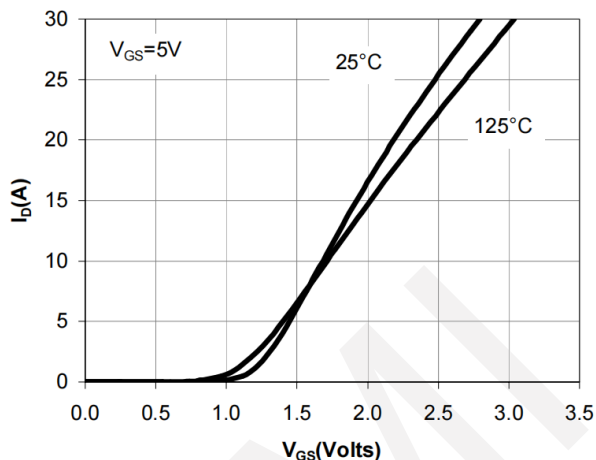


Figure 2 Transfer Characteristics

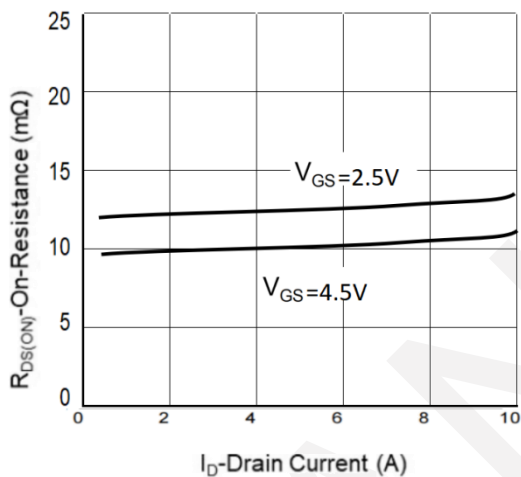


Figure 3 On-Resistance vs. Drain Current and Gate Voltage

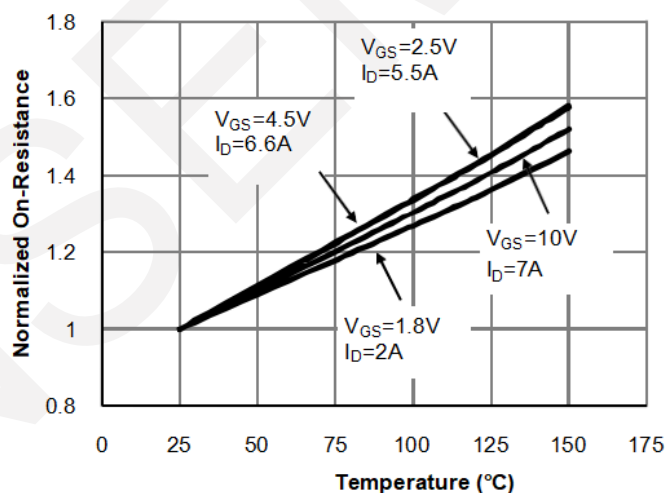


Figure 4 On-Resistance vs. Junction Temperature

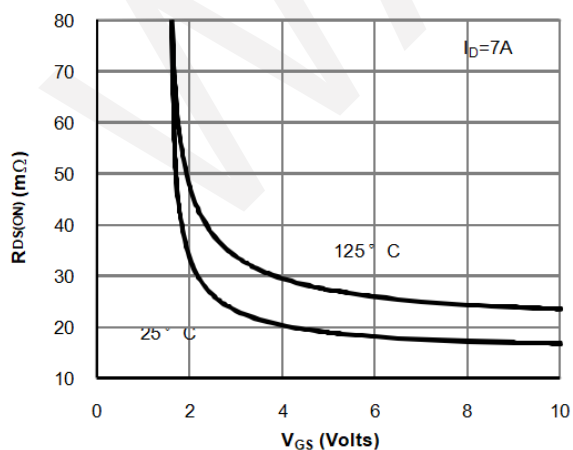


Figure 5 On-Resistance vs. Gate-Source Voltage

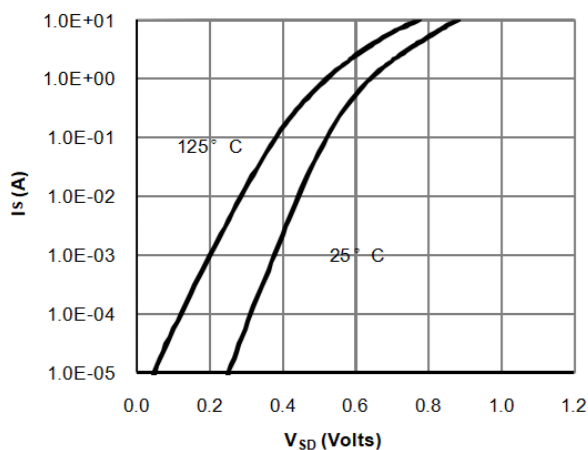
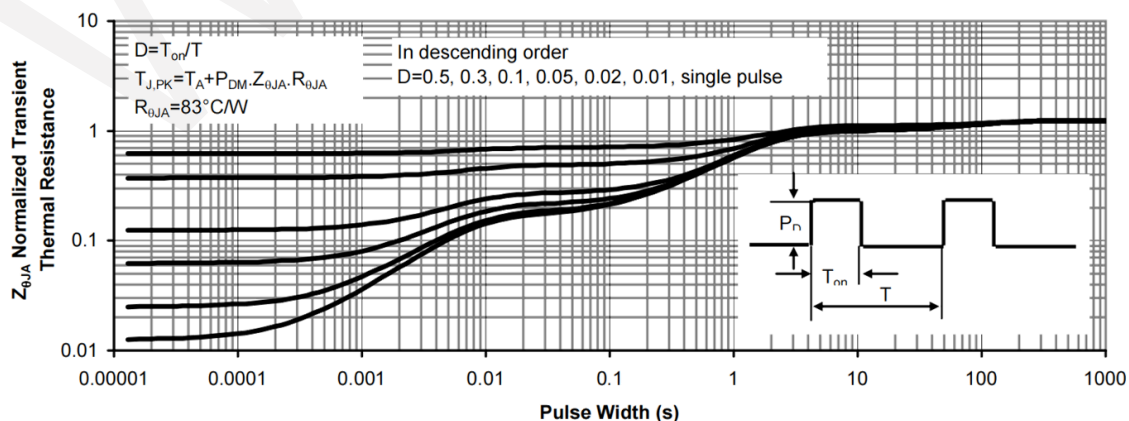
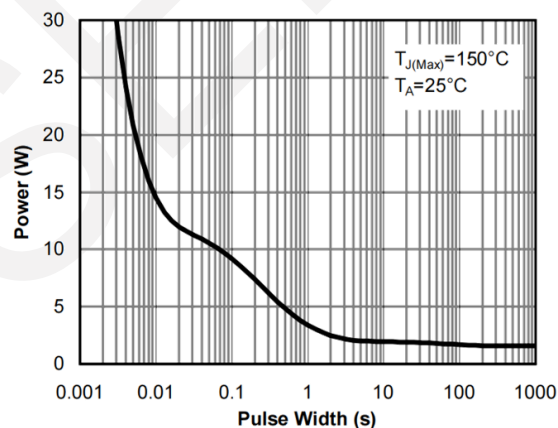
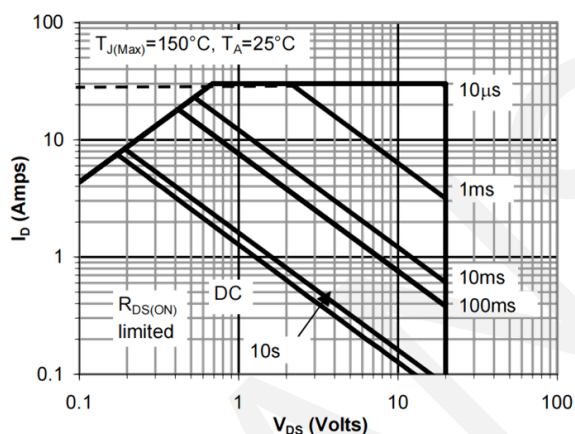
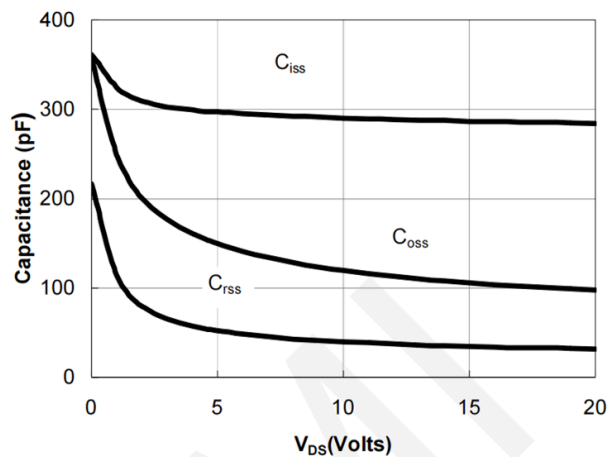
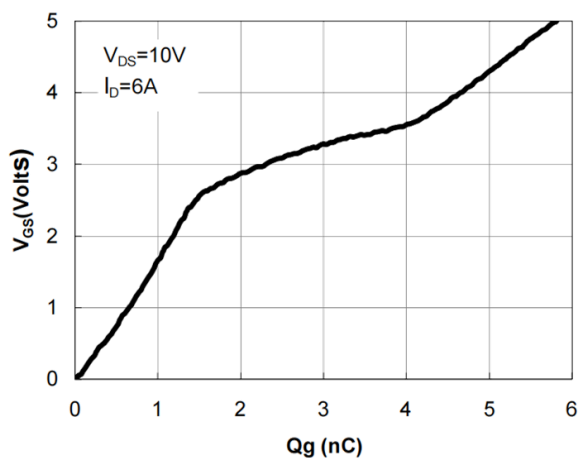
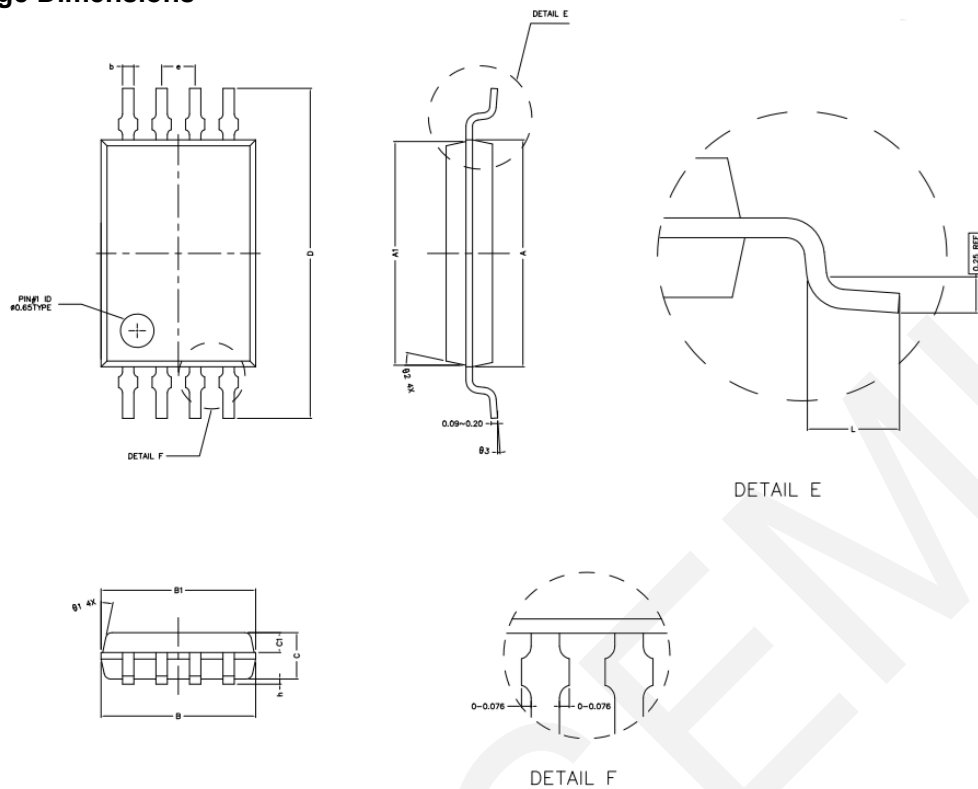


Figure 6 Body-Diode Characteristics



8.Package Dimensions



COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	4.300	4.400	4.500
A1	4.240	4.340	4.440
B	2.900	3.000	3.100
B1	2.840	2.940	3.040
C	0.850	0.900	0.950
C1	0.337	0.387	0.437
D	6.250	6.400	6.550
L	0.450	0.600	0.750
b	0.170	0.220	0.300
h	0.050	0.100	0.150
e	0.650TYPE		
θ_1	12° TYPE		
θ_2	12° TYPE		
θ_3	0° ~ 7°		

9.Important Notice

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